ABSTRACT OF THE DISCLOSURE (FIG. 1)

"LASER ANNEALING METHOD AND APPARATUS FOR DETERMINING LASER ANNEALING CONDITIONS"

A laser annealing method includes preparing a plurality of polycrystalline silicon film samples having different grains sizes, obtaining the energy density condition corresponding to the polycrystalline silicon film sample having the highest degree of scattering, adding a certain value of the energy density to the energy density condition obtained in the preceding step so as to determine a set value of the energy density, and irradiating the amorphous silicon thin film with a laser beam at the set value of the energy density determined in the preceding step so as to carry out the laser annealing.



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